

# SHINDENGEN

## VX-2 Series Power MOSFET

N-Channel Enhancement type

### 2SK2180 (F3V50VX2)

500V3A

#### FEATURES

Input capacitance ( $C_{iss}$ ) is small.  
Especially, input capacitance at 0 bias is small.  
The static  $R_{ds(on)}$  is small.  
The switching time is fast.

#### APPLICATION

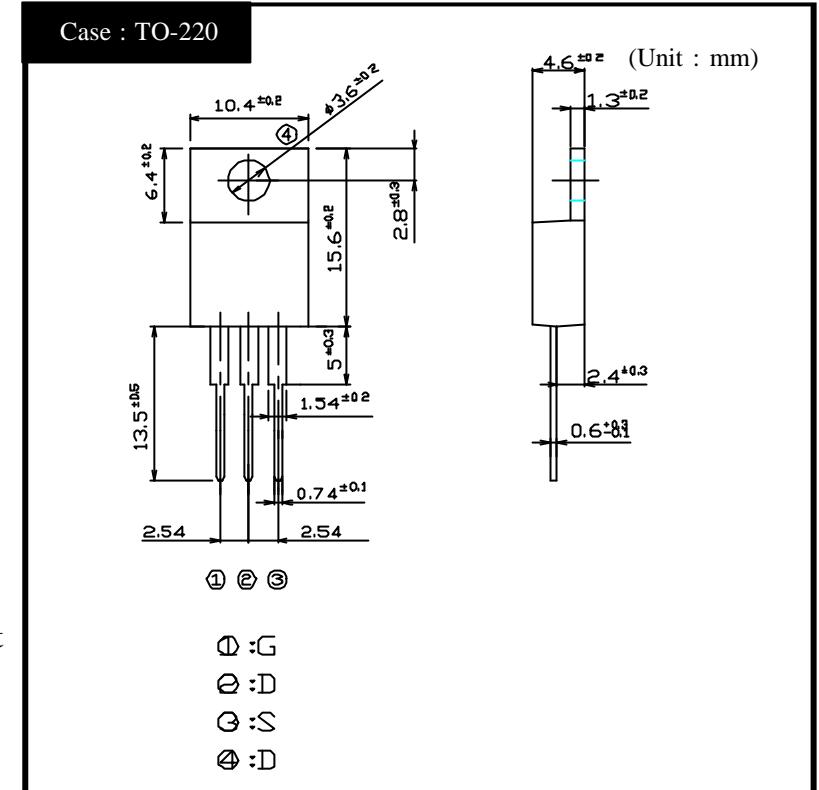
Switching power supply of AC 100V input  
High voltage power supply  
Inverter

#### RATINGS

Absolute Maximum Ratings (T<sub>c</sub> = 25 °C)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T <sub>stg</sub>		-55 ~ 150	
Channel Temperature	T <sub>ch</sub>		150	
Drain-Source Voltage	V <sub>DSS</sub>		500	V
Gate-Source Voltage	V <sub>GSS</sub>		± 30	
Continuous Drain Current (DC)	I <sub>D</sub>		3	
Continuous Drain Current (Peak)	I <sub>DP</sub>		9	A
Continuous Source Current (DC)	I <sub>S</sub>		3	
Total Power Dissipation	P <sub>T</sub>		40	W
Single Pulse Avalanche Current	I <sub>AS</sub>	T <sub>ch</sub> = 25	3	A
Mounting Torque	T <sub>OR</sub>	(Recommended torque : 0.3 N·m)	0.5	N·m

#### OUTLINE DIMENSIONS



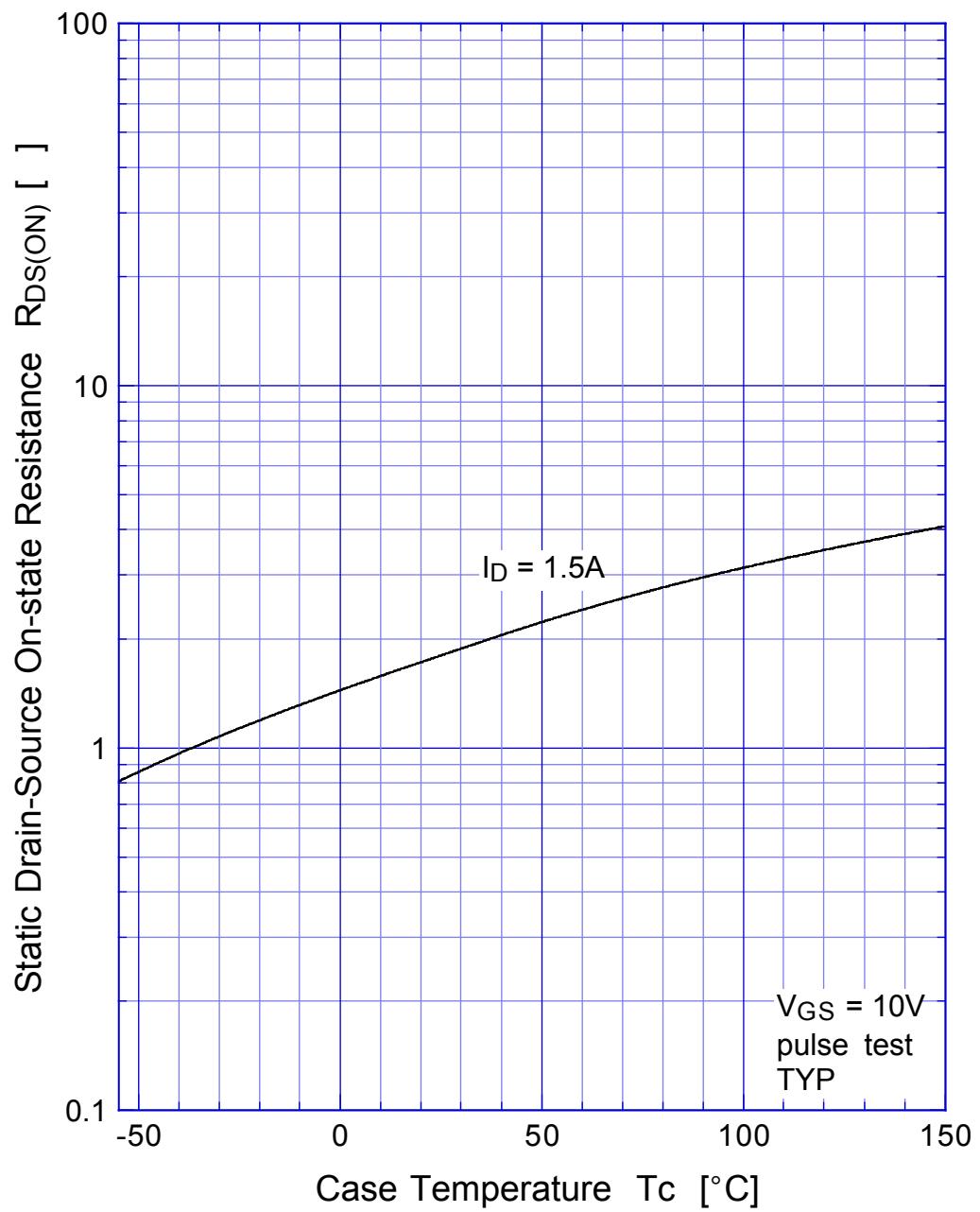
# VX-2 Series Power MOSFET

**2SK2180 ( F3V50VX2 )**

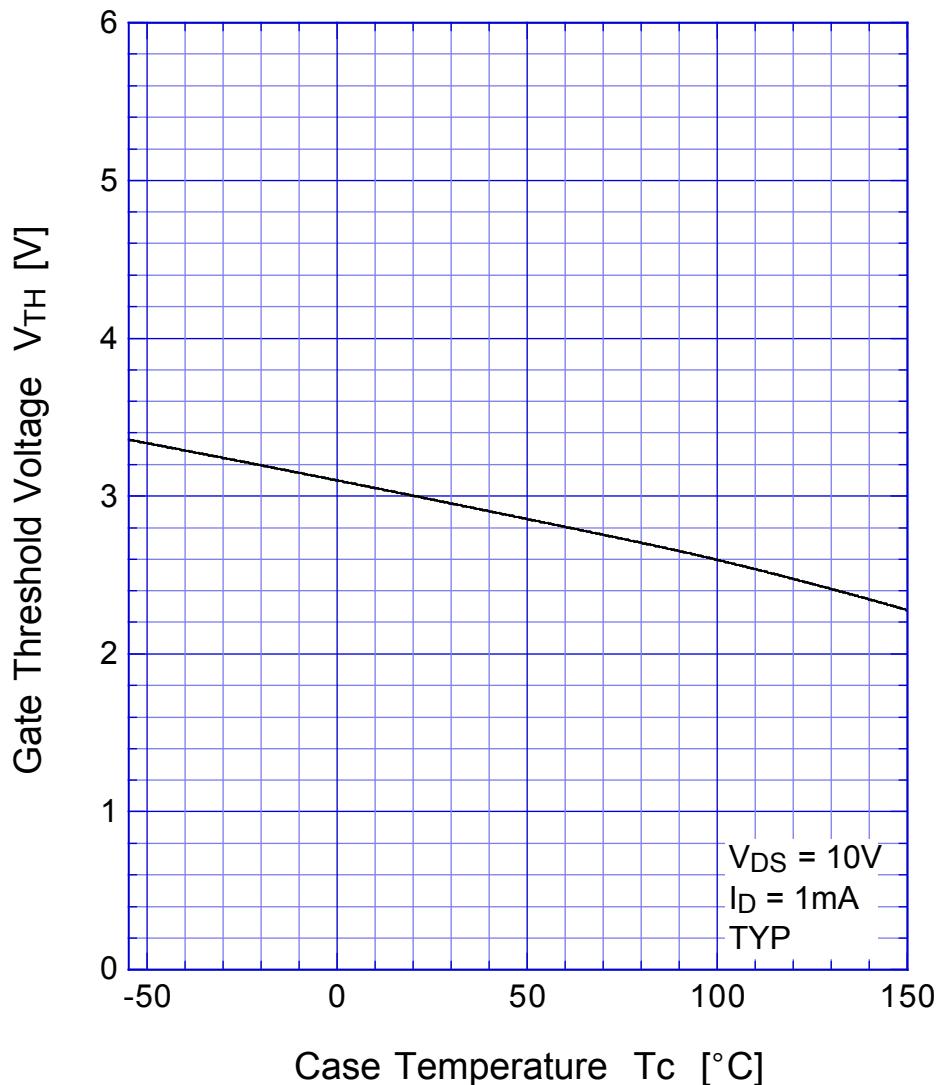
●Electrical Characteristics T<sub>c</sub> = 25°C

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	ID = 1mA, V <sub>GS</sub> = 0V	500			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 500V, V <sub>GS</sub> = 0V			250	μ A
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V			±0.1	
Forward Transconductance	g <sub>fS</sub>	ID = 1.5A, V <sub>DS</sub> = 10V	0.9	2.1		S
Static Drain-Source On-state Resistance	R <sub>D(S)ON</sub>	ID = 1.5A, V <sub>GS</sub> = 10V		1.8	2.3	Ω
Gate Threshold Voltage	V <sub>TH</sub>	ID = 0.3mA, V <sub>DS</sub> = 10V	2.5	3.0	3.5	V
Source-Drain Diode Forwade Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1.5A, V <sub>GS</sub> = 0V			1.5	
Thermal Resistance	θ <sub>jc</sub>	junction to case			3.12	°C/W
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> = 400V, V <sub>GS</sub> = 10V, ID = 3A		15		nC
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		400		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			30		
Output Capacitance	C <sub>oss</sub>			90		
Turn-On Time	t <sub>on</sub>	ID = 1.5A, V <sub>GS</sub> = 10V, R <sub>L</sub> = 100 Ω		45	80	ns
Turn-Off Time	t <sub>off</sub>			90	140	

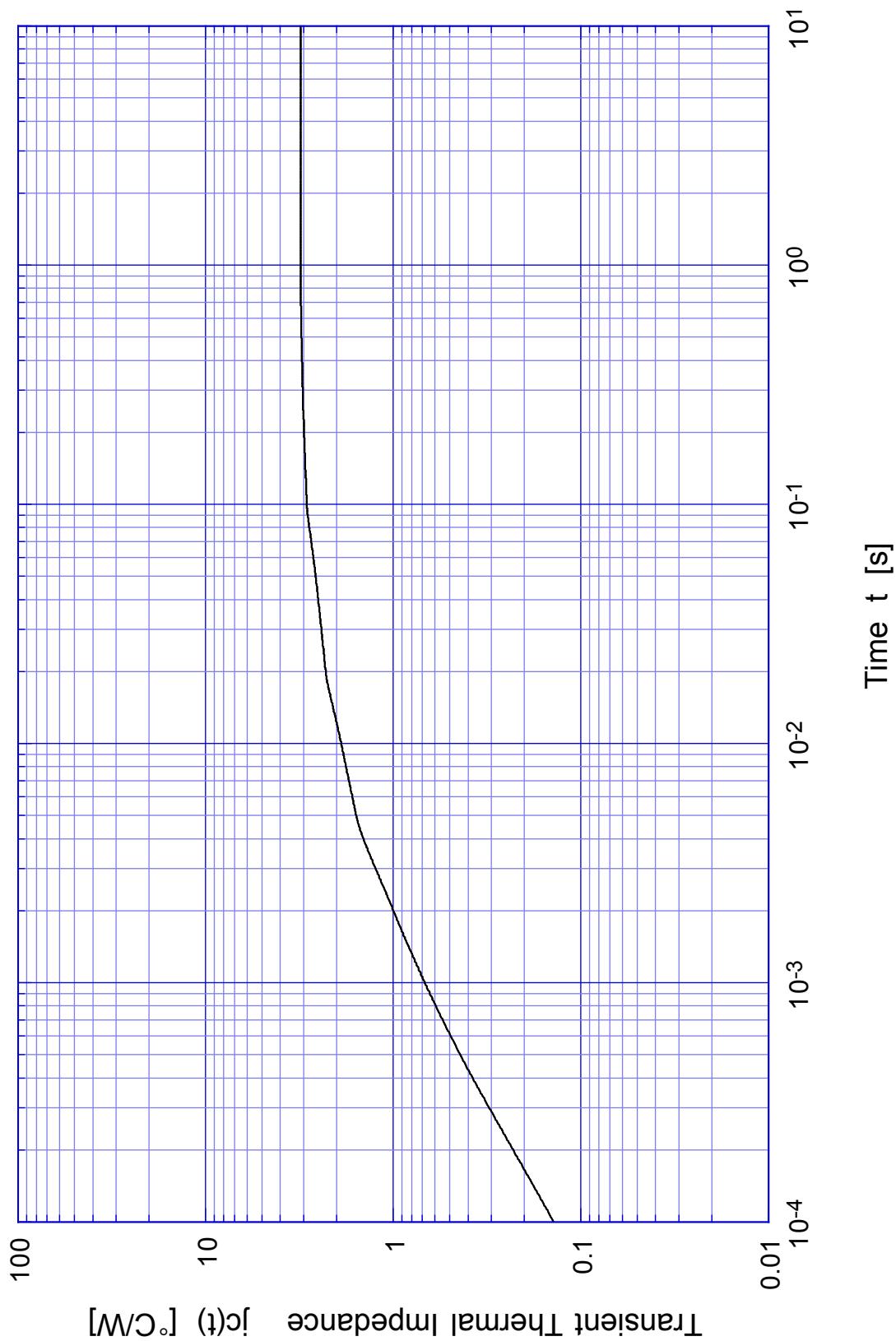
## **2SK2180 Static Drain-Source On-state Resistance**



## **2SK2180      Gate Threshold Voltage**



## 2SK2180 Transient Thermal Impedance



**2SK2180**

Power Derating

